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MEMC 98-3052/2512.2 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster Serial No. 10/038,084 Filed January 3, 2002 Confirmation No. 7363

Art Unit 2814

SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY DEVICE LAYER AND A PROCESS FOR THE PREPARATION THEREOF

Examiner A. D. Mai

October 24, 2003

TO THE COMMISSIONER OF PATENTS AND TRADEMARKS,

SIR:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein.

Respectfully submitted,

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RAS/skd 'Enclosures

PTO/SB/08A				Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/038,084		
				Filing Date	January 3, 2002		
(use	as many she	ets as	necessary)	Confirmation Number	7363		
		£	2 4 2013 THE	First Named Inventor	Robert J. Falster 📇		
		OCT	VI & TP. Market	Group Art Unit	2814 00 77 2		
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Sheet	1	of	1 ,	Attorney Docket No.	MEMC 98-3052/2512.2		

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1			U	.S. PATEN	T DOCUMENTS			
	Cite No.1	U.S. Patent Document						
Examiner Initials*			Number ,	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY		
	121	6,180,2	20	B1	Falster et al.	01-30-2001		
	122	6,221,7	43	B1	Fujikawa et al.	04-24-2001		
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	124	5,194,3	5,194,395 Wada 03-16-1				3-16-1993:	
			FOR	EIGN PATE	ENT DOCUMENTS			
Examiner Initials*	Cite No. ¹	Foreign Patent Document						
		Office	Number⁴	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY		
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	•	OTH	IER ART - N	ON PATEN	T LITERATURE DOCUMEN	TS	•	
Examiner Initials*	Cite No.1 Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.							
	125	Internat	ional Search Rei	oort for analogo	us application No. PCT/US02/19906 o	lated May 8, 2003.		

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Signature	1.		Considered		
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached.